



SS/eng
#579
1-15-02

PATENT APPLICATION

THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Kazuhiko OKAWA et al.

Application No.: 09/866,800

Filed: May 30, 2001

Docket No.: 109657

For: SEMICONDUCTOR DEVICE HAVING ELECTROSTATIC PROTECTION CIRCUIT
AND METHOD OF FABRICATING THE SAME

PRELIMINARY AMENDMENT

Director of the U.S. Patent and Trademark Office
Washington, D. C. 20231

Sir:

Prior to initial examination, please amend the above-identified application as follows:

IN THE SPECIFICATION:

Page 5, lines 22-27 and Page 6, lines 1-14 delete current paragraph and insert therefor:

According to one aspect of the present invention, there is provided a semiconductor device comprising:

a semiconductor substrate;

a MOS transistor which is formed on the semiconductor substrate and includes a first diffusion region;

a first isolation region which isolates the MOS transistor from other MOS transistors on the semiconductor substrate;

a second isolation region formed between the MOS transistor and the first isolation region;